

# MOSFET – N-Channel, POWERTRENCH<sup>®</sup>

**100 V, 300 A, 2.0 mΩ**

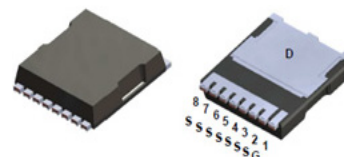
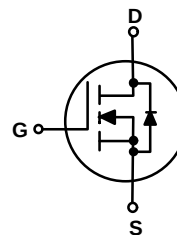
**FDBL86062-F085**

## Features

- Typical  $R_{DS(on)} = 1.5 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 80 \text{ A}$
- Typical  $Q_{g(tot)} = 95 \text{ nC}$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 80 \text{ A}$
- UIS Capability
- Qualified to AEC Q101
- This Device is Pb-Free and is RoHS Compliant

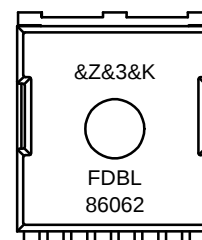
## Applications

- Automotive Engine Control
- PowerTrain Management
- Solenoid and Motor Drivers
- Integrated Starter/Alternator
- Primary Switch for 12 V Systems



**H-PSOF8L 11.68x9.80  
CASE 100CU**

## MARKING DIAGRAM



|           |                           |
|-----------|---------------------------|
| &Z        | = Assembly Plant Code     |
| &3        | = Data Code (Year & Week) |
| &K        | = Lot Code                |
| FDBL86062 | = Specific Device Code    |

## ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FDBL86062-F085

## MOSFET MAXIMUM RATINGS $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol          | Parameter                                                | Rating                   | Units               |
|-----------------|----------------------------------------------------------|--------------------------|---------------------|
| $V_{DSS}$       | Drain-to-Source Voltage                                  | 100                      | V                   |
| $V_{GS}$        | Gate-to-Source Voltage                                   | $\pm 20$                 | V                   |
| $I_D$           | Drain Current - Continuous ( $V_{GS} = 10$ ) (Note 1)    | $T_C = 25^\circ\text{C}$ | A                   |
|                 | Pulsed Drain Current                                     | $T_C = 25^\circ\text{C}$ |                     |
| $E_{AS}$        | Single Pulse Avalanche Energy (Note 2)                   | 352                      | mJ                  |
| $P_D$           | Power Dissipation                                        | 429                      | W                   |
|                 | Derate Above $25^\circ\text{C}$                          | 2.9                      | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$  | Operating and Storage Temperature                        | $-55$ to $+175$          | $^\circ\text{C}$    |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case                     | 0.35                     | $^\circ\text{C/W}$  |
| $R_{\theta JA}$ | Maximum Thermal Resistance, Junction to Ambient (Note 3) | 43                       | $^\circ\text{C/W}$  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Current is limited by silicon.
- Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.1$  mH,  $I_{AS} = 84$  A,  $V_{DD} = 100$  V during inductor charging and  $V_{DD} = 0$  V during time in avalanche.
- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

## PACKAGE MARKING AND ORDERING INFORMATION

| Device Marking | Device         | Package  | Reel Size | Tape Width | Quantity   |
|----------------|----------------|----------|-----------|------------|------------|
| FDBL86062      | FDBL86062-F085 | H-PSOF8L | 13"       | 24 mm      | 2000 Units |

## ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ , unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|-------|

### OFF CHARACTERISTICS

|            |                                   |                                          |                                    |   |           |                 |
|------------|-----------------------------------|------------------------------------------|------------------------------------|---|-----------|-----------------|
| $B_{VDSS}$ | Drain-to-Source Breakdown Voltage | $I_D = 250 \mu\text{A}$ , $V_{GS} = 0$ V | 100                                | – | –         | V               |
| $I_{DSS}$  | Drain-to-Source Leakage Current   | $V_{DS} = 100$ V,<br>$V_{GS} = 0$ V      | $T_J = 25^\circ\text{C}$           | – | –         | 5 $\mu\text{A}$ |
|            |                                   |                                          | $T_J = 175^\circ\text{C}$ (Note 4) | – | –         | 2 mA            |
| $I_{GSS}$  | Gate-to-Source Leakage Current    | $V_{GS} = \pm 20$ V                      | –                                  | – | $\pm 100$ | nA              |

### ON CHARACTERISTICS

|              |                                  |                                             |                                    |     |     |                |
|--------------|----------------------------------|---------------------------------------------|------------------------------------|-----|-----|----------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}$ , $I_D = 250 \mu\text{A}$ | 2.0                                | 3.1 | 4.5 | V              |
| $R_{DS(on)}$ | Drain to Source On Resistance    | $I_D = 80$ A,<br>$V_{GS} = 10$ V            | $T_J = 25^\circ\text{C}$           | –   | 1.5 | 2.0 m $\Omega$ |
|              |                                  |                                             | $T_J = 175^\circ\text{C}$ (Note 4) | –   | 3.3 | 4.3            |

### DYNAMIC CHARACTERISTICS

|              |                               |                                                 |                                 |      |    |          |
|--------------|-------------------------------|-------------------------------------------------|---------------------------------|------|----|----------|
| $C_{iss}$    | Input Capacitance             | $V_{DS} = 50$ V, $V_{GS} = 0$ V,<br>$f = 1$ MHz | –                               | 6970 | –  | pF       |
| $C_{oss}$    | Output Capacitance            |                                                 | –                               | 3950 | –  |          |
| $C_{rss}$    | Reverse Transfer Capacitance  |                                                 | –                               | 29   | –  |          |
| $R_g$        | Gate Resistance               | $f = 1$ MHz                                     | –                               | 0.4  | –  | $\Omega$ |
| $Q_{g(ToT)}$ | Total Gate Charge at 10 V     | $V_{GS} = 0$ to 10 V                            | $V_{DD} = 80$ V<br>$I_D = 80$ A | –    | 95 | nC       |
| $Q_{g(th)}$  | Threshold Gate Charge         | $V_{GS} = 0$ to 2 V                             |                                 | –    | 13 |          |
| $Q_{gs}$     | Gate-to-Source Gate Charge    |                                                 |                                 | –    | 31 |          |
| $Q_{gd}$     | Gate-to-Drain "Miller" Charge |                                                 |                                 | –    | 20 |          |
|              |                               |                                                 |                                 |      |    |          |

# FDBL86062-F085

## ELECTRICAL CHARACTERISTICS (continued) $T_J = 25^\circ\text{C}$ , unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|-------|

### SWITCHING CHARACTERISTICS

|              |                |                                                                                                  |   |    |    |    |
|--------------|----------------|--------------------------------------------------------------------------------------------------|---|----|----|----|
| $t_{on}$     | Turn-On Time   | $V_{DD} = 50\text{ V}$ , $I_D = 80\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\ \Omega$ | – | –  | 73 | ns |
| $t_{d(on)}$  | Turn-On Delay  |                                                                                                  | – | 31 | –  |    |
| $t_r$        | Rise Time      |                                                                                                  | – | 25 | –  |    |
| $t_{d(off)}$ | Turn-Off Delay |                                                                                                  | – | 36 | –  |    |
| $t_f$        | Fall Time      |                                                                                                  | – | 9  | –  |    |
| $t_{off}$    | Turn-Off Time  |                                                                                                  | – | –  | 59 |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|          |                               |                                                                                        |   |     |      |    |
|----------|-------------------------------|----------------------------------------------------------------------------------------|---|-----|------|----|
| $V_{SD}$ | Source-to-Drain Diode Voltage | $I_{SD} = 80\text{ A}$ , $V_{GS} = 0\text{ V}$                                         | – | –   | 1.25 | V  |
|          |                               | $I_{SD} = 40\text{ A}$ , $V_{GS} = 0\text{ V}$                                         | – | –   | 1.2  |    |
| $t_{rr}$ | Reverse-Recovery Time         | $I_F = 80\text{ A}$ , $dI_{SD}/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 80\text{ V}$ | – | 115 | 150  | ns |
| $Q_{rr}$ | Reverse-Recovery Charge       |                                                                                        | – | 172 | 224  | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at  $T_J = 175^\circ\text{C}$ . Product is not tested to this condition in production.

TYPICAL CHARACTERISTICS

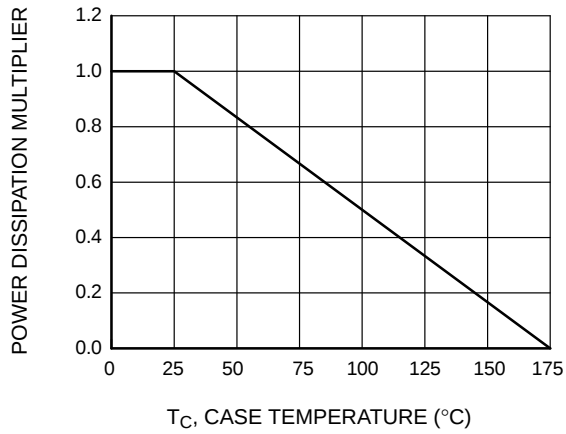


Figure 1. Normalized Power Dissipation vs. Case Temperature

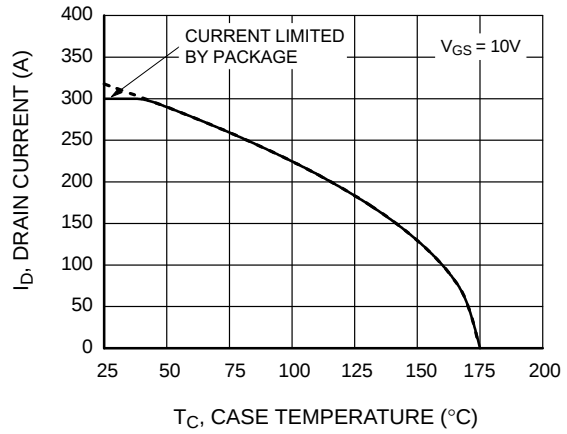


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

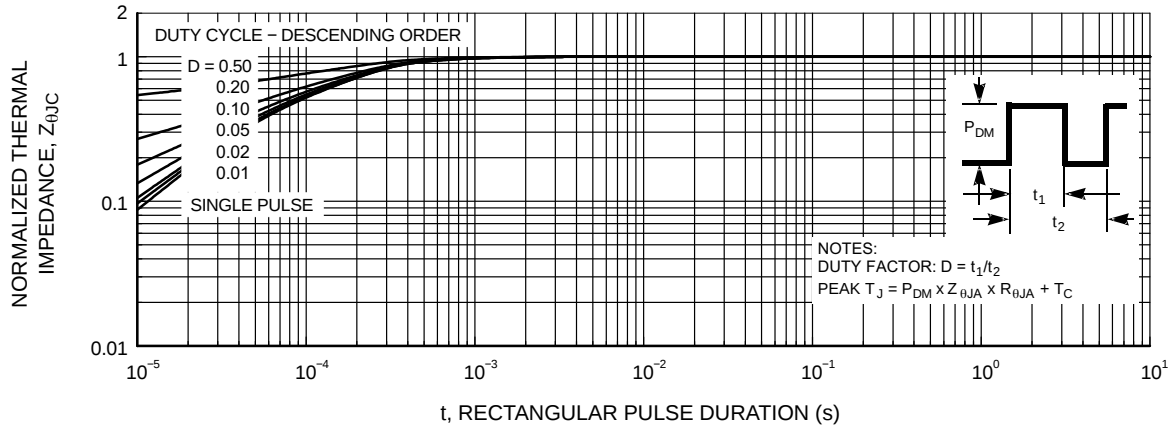


Figure 3. Normalized Maximum Transient Thermal Impedance

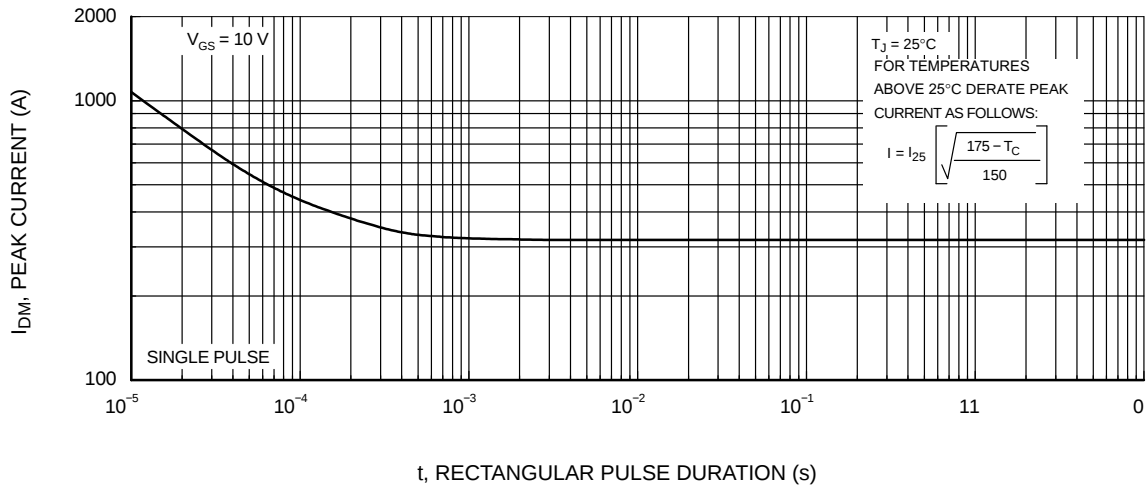


Figure 4. Peak Current Capability

## TYPICAL CHARACTERISTICS (CONTINUED)

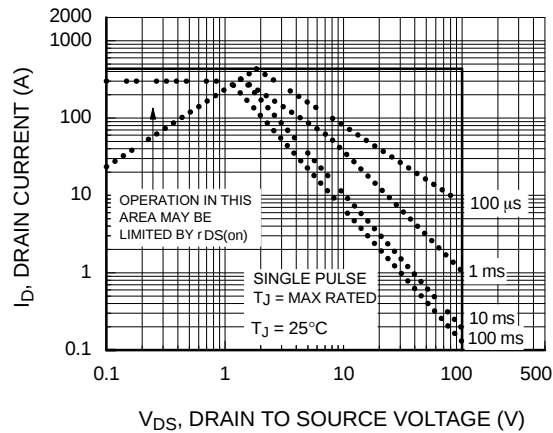
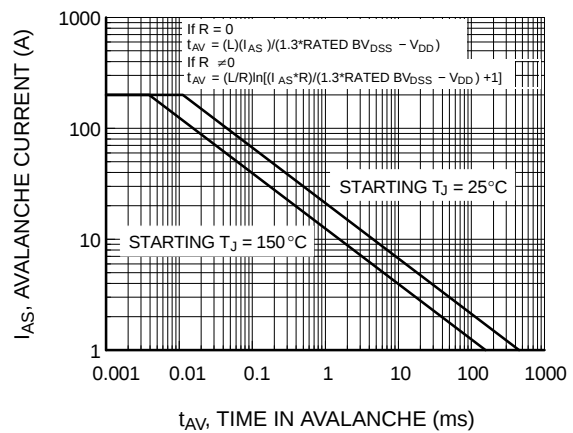


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

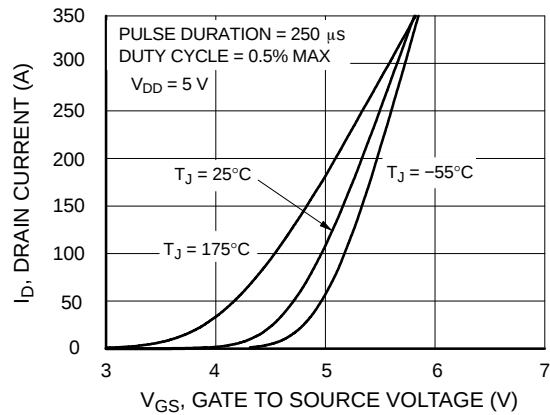


Figure 7. Transfer Characteristics

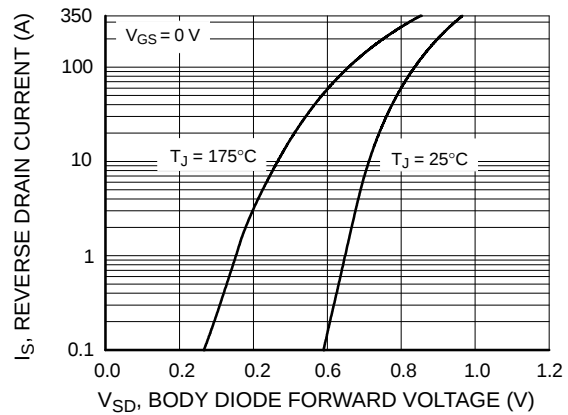


Figure 8. Forward Diode Characteristics

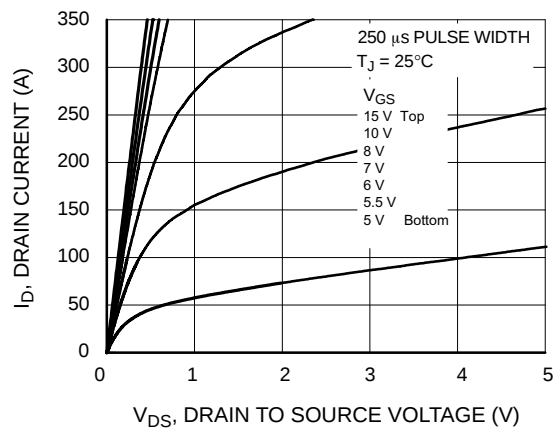


Figure 9. Saturation Characteristics

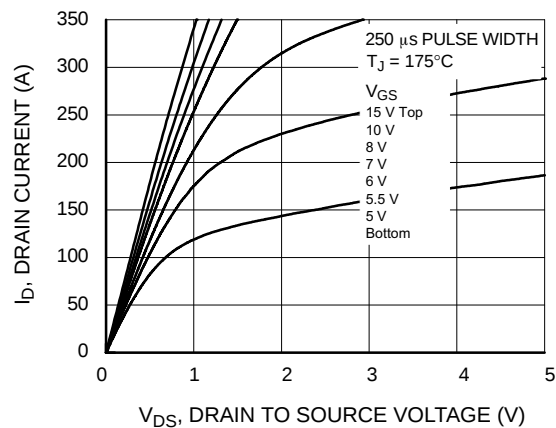


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (CONTINUED)

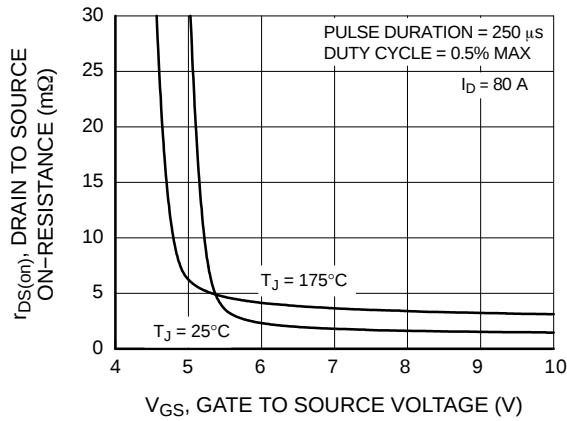


Figure 11.  $R_{DS(on)}$  vs. Gate Voltage

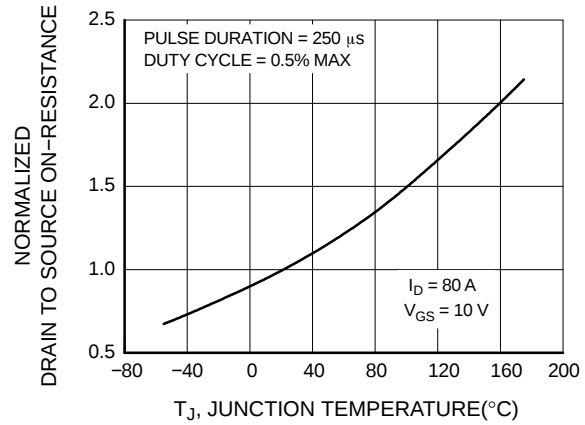


Figure 12. Normalized  $R_{DS(on)}$  vs. Junction Temperature

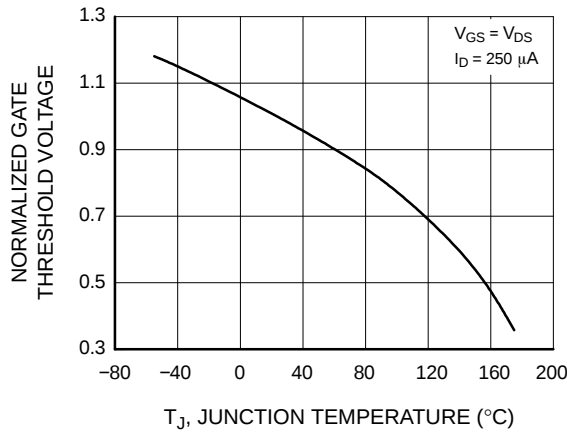


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

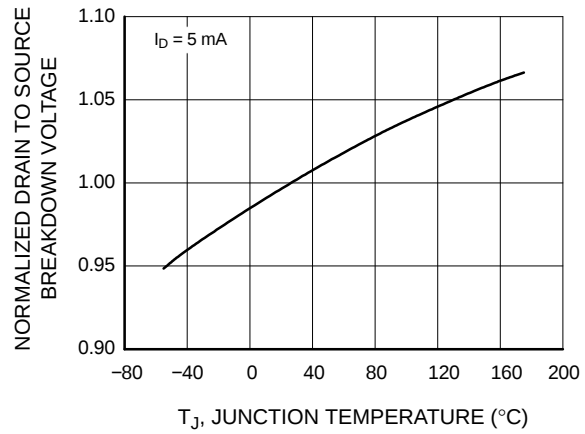


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

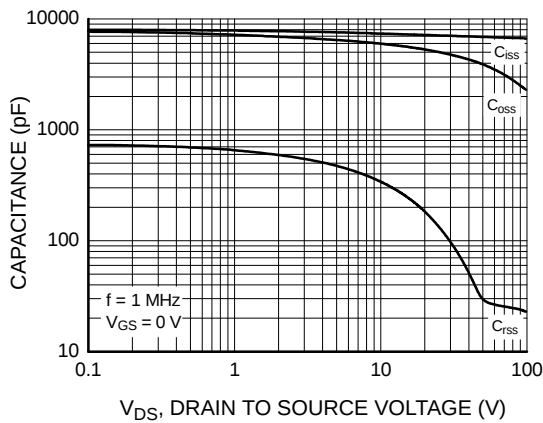


Figure 15. Capacitance vs. Drain to Source Voltage

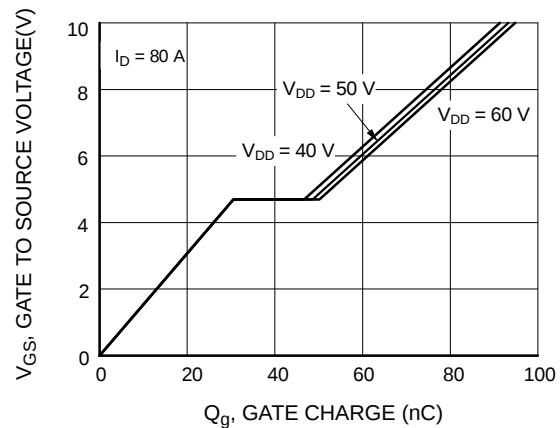
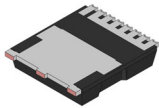
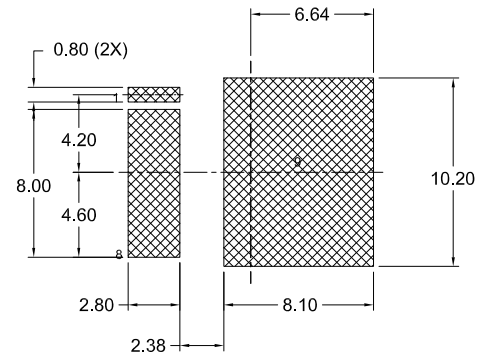
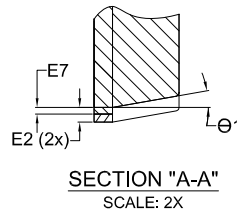
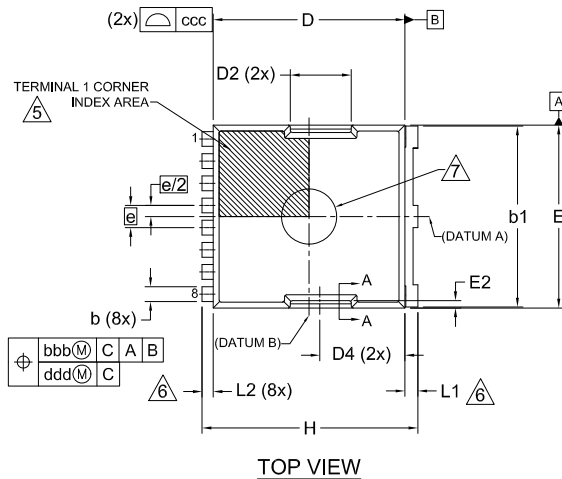


Figure 16. Gate Charge vs. Gate to Source Voltage

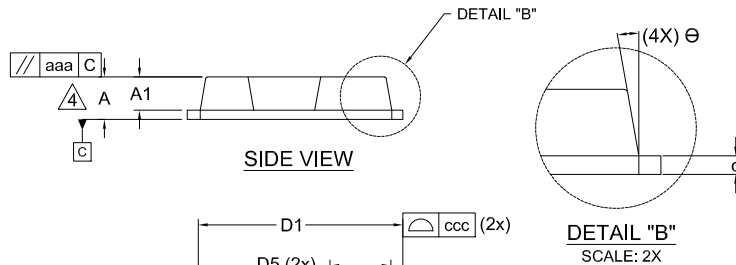


H-PSOF8L 11.68x9.80x2.30, 1.20P  
CASE 100CU  
ISSUE F

DATE 30 JUL 2024

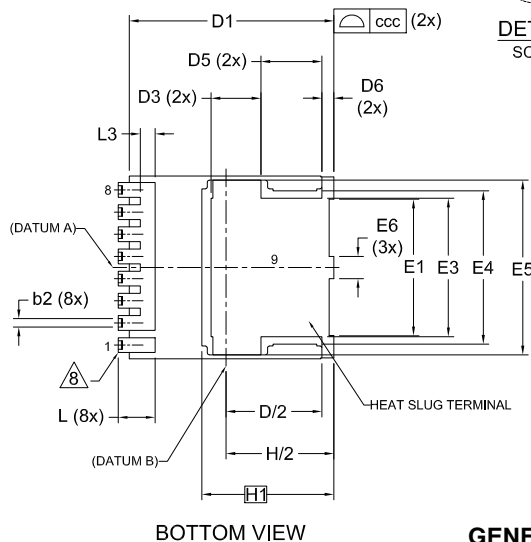


\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



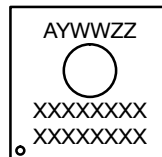
NOTES:

1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g., EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1, L1, L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.



GENERIC  
MARKING DIAGRAM\*

A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code  
XXXX = Specific Device Code



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| DIM | MILLIMETERS |       |       |
|-----|-------------|-------|-------|
|     | MIN.        | NOM.  | MAX.  |
| A   | 2.20        | 2.30  | 2.40  |
| A1  | 1.70        | 1.80  | 1.90  |
| b   | 0.70        | 0.80  | 0.90  |
| b1  | 9.70        | 9.80  | 9.90  |
| b2  | 0.35        | 0.45  | 0.55  |
| c   | 0.40        | 0.50  | 0.60  |
| D   | 10.28       | 10.38 | 10.48 |
| D/2 | 5.09        | 5.19  | 5.29  |
| D1  | 10.98       | 11.08 | 11.18 |
| D2  | 3.20        | 3.30  | 3.40  |
| D3  | 2.60        | 2.70  | 2.80  |
| D4  | 4.45        | 4.55  | 4.65  |
| D5  | 3.20        | 3.30  | 3.40  |
| D6  | 0.55        | 0.65  | 0.75  |
| E   | 9.80        | 9.90  | 10.00 |
| E1  | 7.30        | 7.40  | 7.50  |
| E2  | 0.30        | 0.40  | 0.50  |
| E3  | 7.40        | 7.50  | 7.60  |
| E4  | 8.20        | 8.30  | 8.40  |

| DIM | MILLIMETERS |       |       |
|-----|-------------|-------|-------|
|     | MIN.        | NOM.  | MAX.  |
| E5  | 9.36        | 9.46  | 9.56  |
| E6  | 1.10        | 1.20  | 1.30  |
| E7  | 0.15        | 0.18  | 0.21  |
| e   | 1.20 BSC    |       |       |
| e/2 | 0.60 BSC    |       |       |
| H   | 11.58       | 11.68 | 11.78 |
| H/2 | 5.74        | 5.84  | 5.94  |
| H1  | 7.15 BSC    |       |       |
| L   | 1.90        | 2.00  | 2.10  |
| L1  | 0.60        | 0.70  | 0.80  |
| L2  | 0.50        | 0.60  | 0.70  |
| L3  | 0.70        | 0.80  | 0.90  |
| Θ   | 10° REF     |       |       |
| Θ1  | 10° REF     |       |       |
| aaa | 0.20        |       |       |
| bbb | 0.25        |       |       |
| ccc | 0.20        |       |       |
| ddd | 0.20        |       |       |
| eee | 0.10        |       |       |

DOCUMENT NUMBER: 98AON13813G

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DESCRIPTION: H-PSOF8L 11.68x9.80x2.30, 1.20P

PAGE 1 OF 1

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